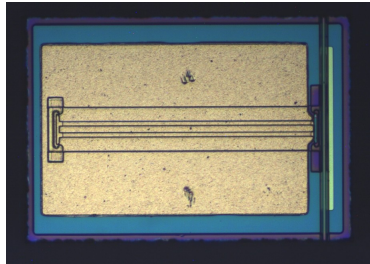


# Vertical Emission Laser Chip

VL13000020



### Feature

- High power and efficiency
- Cathode bond pad on bottom side.
- Operation temperature -40~85°C

### Device Electro-Optical Characteristics

All parameters for T = 25°C unless otherwise noted.

PARAMETER	SYMBOL	UNIT	MIN.	TYP.	MAX.	TEST CONDITIONS
Output power	P	mW	300			I = 400mA
Operating Voltage	V <sub>f</sub>	Volt	1.4		2	I = 400mA
Wavelength	λ	nm	1270		1360	I = 400mA

### Device Physical Specifications Single Chip

PARAMETER	UNIT	MIN.	TYP.	MAX.
Bond Pad	um		300*85 X2	
Chip size	um	420*285	435*300	450*315
Chip Hight	um	135	150	165

### Absolute Maximum Ratings

PARAMETER	SYMBOL	UNIT	Ratings
Forward Current	I	mA	450
Reverse Voltage	V <sub>r</sub>	Volt	1
Operating Temperature	T <sub>o</sub>	°C	-40 to +85
Storage Temperature (Chip on Tape)	T <sub>st</sub>	°C	5 to +35
Soldering Temperature	T <sub>so</sub>	°C	260 @10sec

### Order Information

VL13000010-A01: Vertical Emission Laser Chip